

1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) surface mountable plastic package. This triac is intended for use in motor control circuits where high blocking voltage, high static and dynamic dV_D/dt as well as high dI_{com}/dt can occur. This "series C0T" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber. This device has high operating capability ($T_{j(max)} = 150\text{ °C}$)

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High junction operating temperature capability ($T_{j(max)} = 150\text{ °C}$)
- High immunity to false turn-on by dV/dt
- High voltage capability
- Less sensitive gate for very high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Applications subject to high temperature ($T_{j(max)} = 150\text{ °C}$)
- Compressor starting control circuits
- General purpose motor controls
- Reversing induction motor controls e.g. vertical axis washing machines

4. Quick reference data

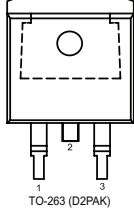

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V _{DRM}	repetitive peak off-state voltage			800			V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 134 °C; Fig. 1 ; Fig. 2 ; Fig. 3		8			A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; Fig. 4 ; Fig. 5		60			A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms		65			A
T _j	junction temperature			150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		5	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		5	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		5	-	35	mA

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	50	mA
V_T	on-state voltage	$I_T = 10\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.30	1.65	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		2000	-	-	V/ μs
		$V_{DM} = 536\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		1500	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_J = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 8\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit		7	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-263 (D2PAK)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA308B-800C0T	TO263	BTA308B-800C0TJ	Reel	800	TO263N	26-Sep-2016

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA308B-800C0T	BTA308B 800C0T

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 134\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5		60	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$		65	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; SIN		18	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 70\text{ mA}$		100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			2	A
P_{GM}	peak gate power			5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		0.5	W
T_{stg}	storage temperature			-40 to 150	$^{\circ}\text{C}$
T_{j}	junction temperature			150	$^{\circ}\text{C}$

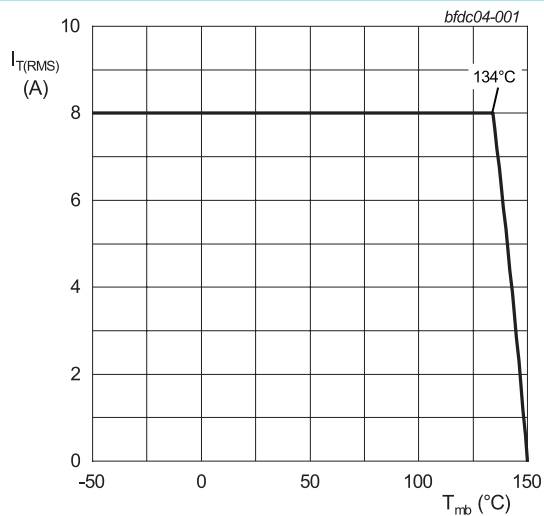
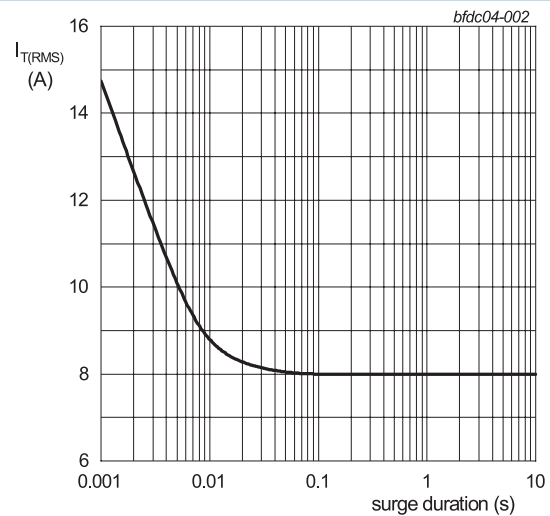


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{\text{mb}} = 134\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

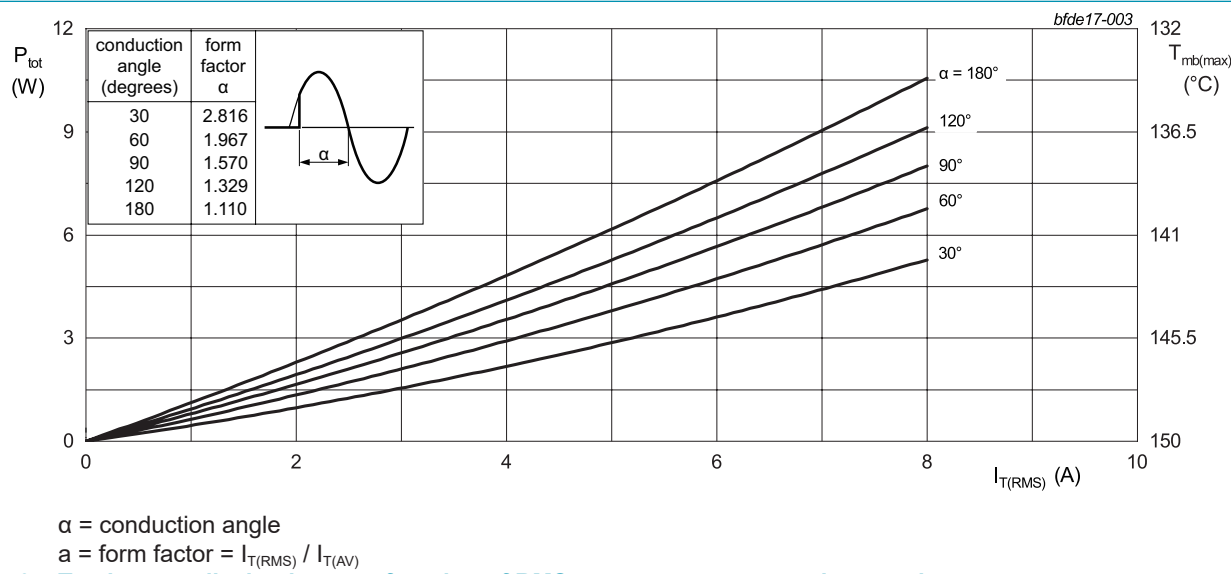


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

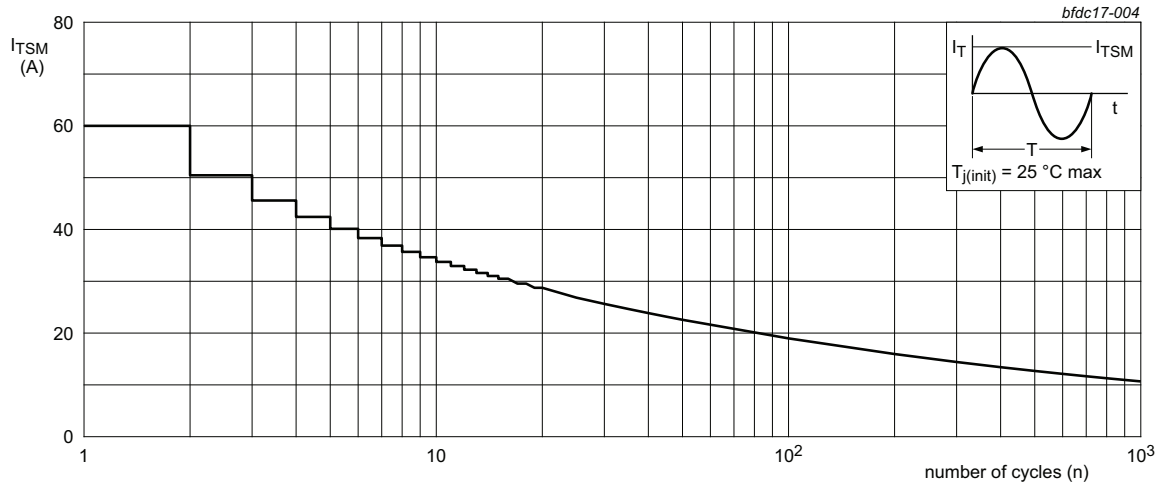


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

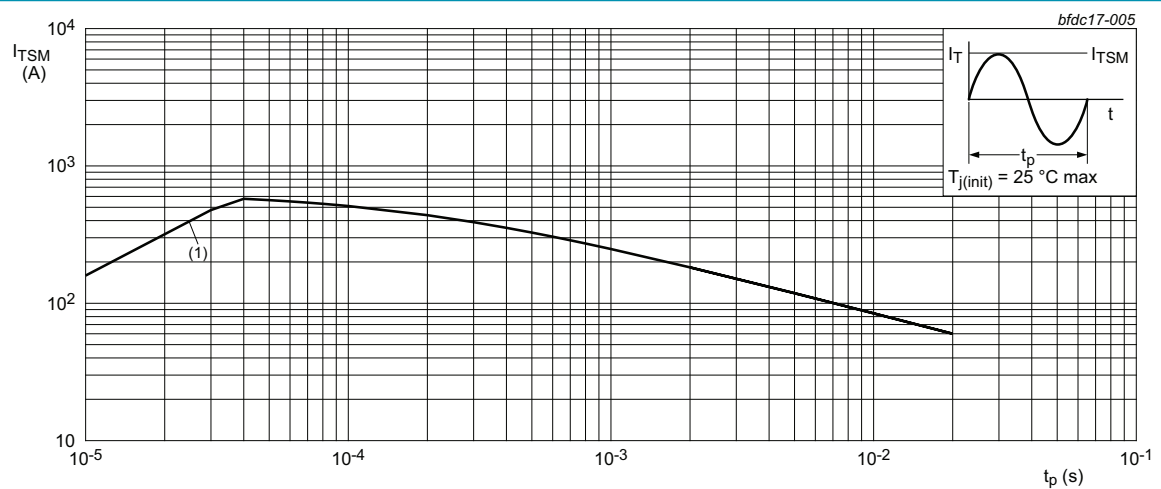


Fig. 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

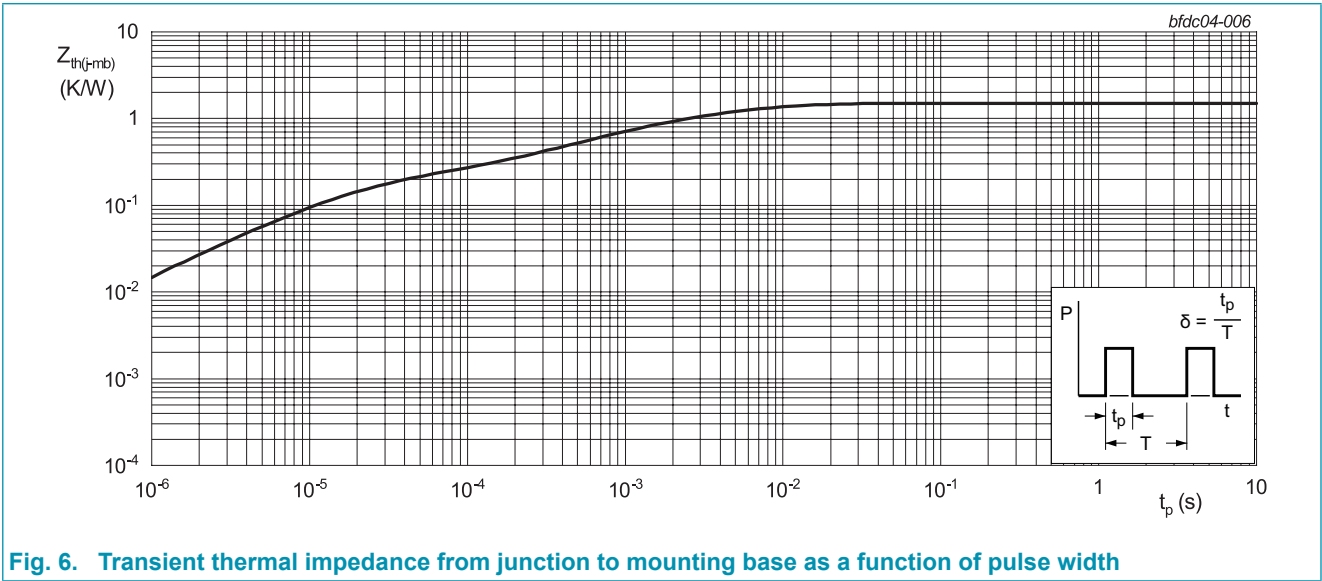
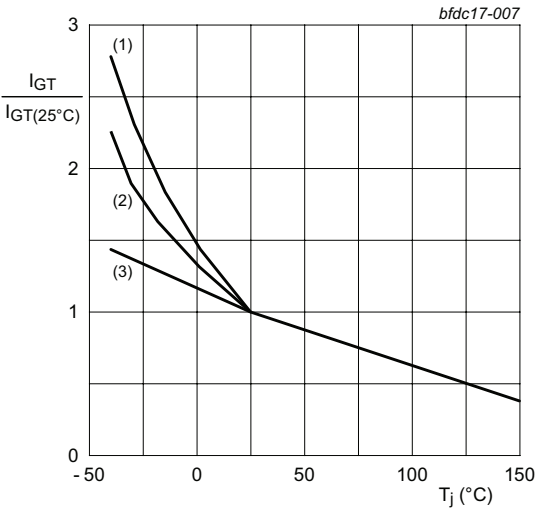


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _J = 25 °C; Fig. 7		5	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _J = 25 °C; Fig. 7		5	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _J = 25 °C; Fig. 7		5	-	35	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _J = 25 °C; Fig. 8		-	-	50	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _J = 25 °C; Fig. 8		-	-	75	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _J = 25 °C; Fig. 8		-	-	50	mA
I _H	holding current	V _D = 12 V; T _J = 25 °C; Fig. 9		-	-	50	mA
V _T	on-state voltage	I _T = 10 A; T _J = 25 °C; Fig. 10		-	1.30	1.65	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _J = 25 °C; Fig. 11		-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _J = 150 °C		0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _J = 25 °C		-	-	10	μA
		V _D = 800 V; T _J = 150 °C		-	-	1	mA
I _R	reverse current	V _D = 800 V; T _J = 25 °C		-	-	10	μA
		V _D = 800 V; T _J = 150 °C		-	-	1	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _J = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		2000	-	-	V/μs
		V _{DM} = 536 V; T _J = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1500	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _J = 150 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit		7	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

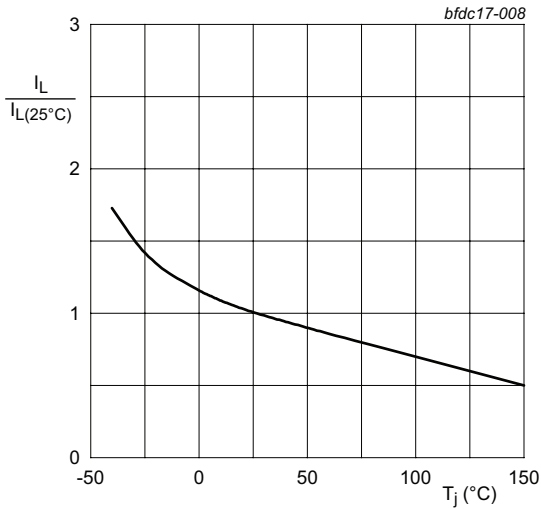


Fig. 8. Normalized latching current as a function of junction temperature

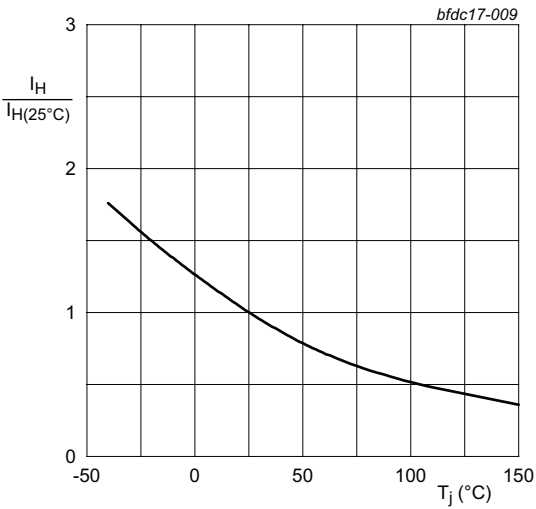
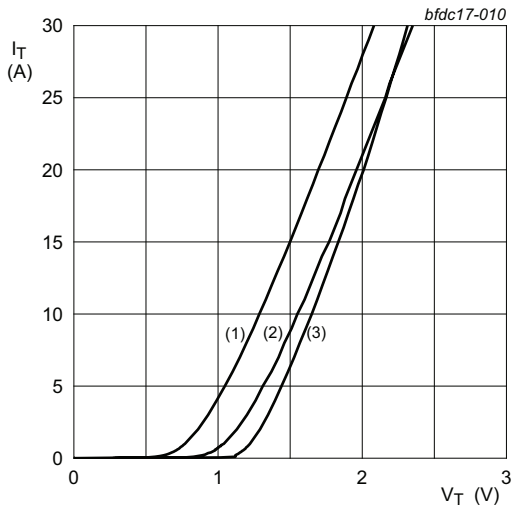


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.210\text{ V}; R_s = 0.0288\ \Omega$
- (1) $T_j = 150^{\circ}\text{C}$; typical values
 - (2) $T_j = 150^{\circ}\text{C}$; maximum values
 - (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

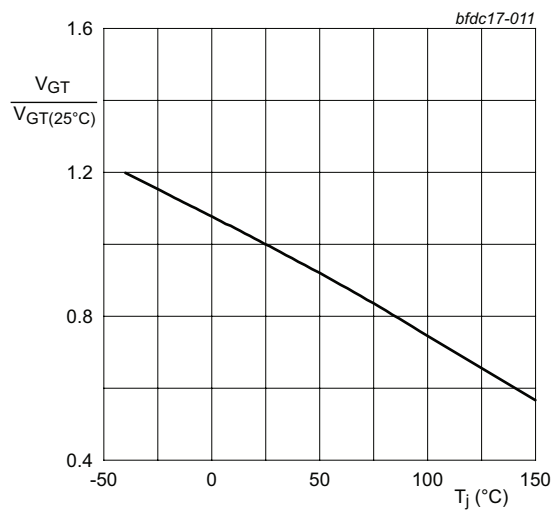
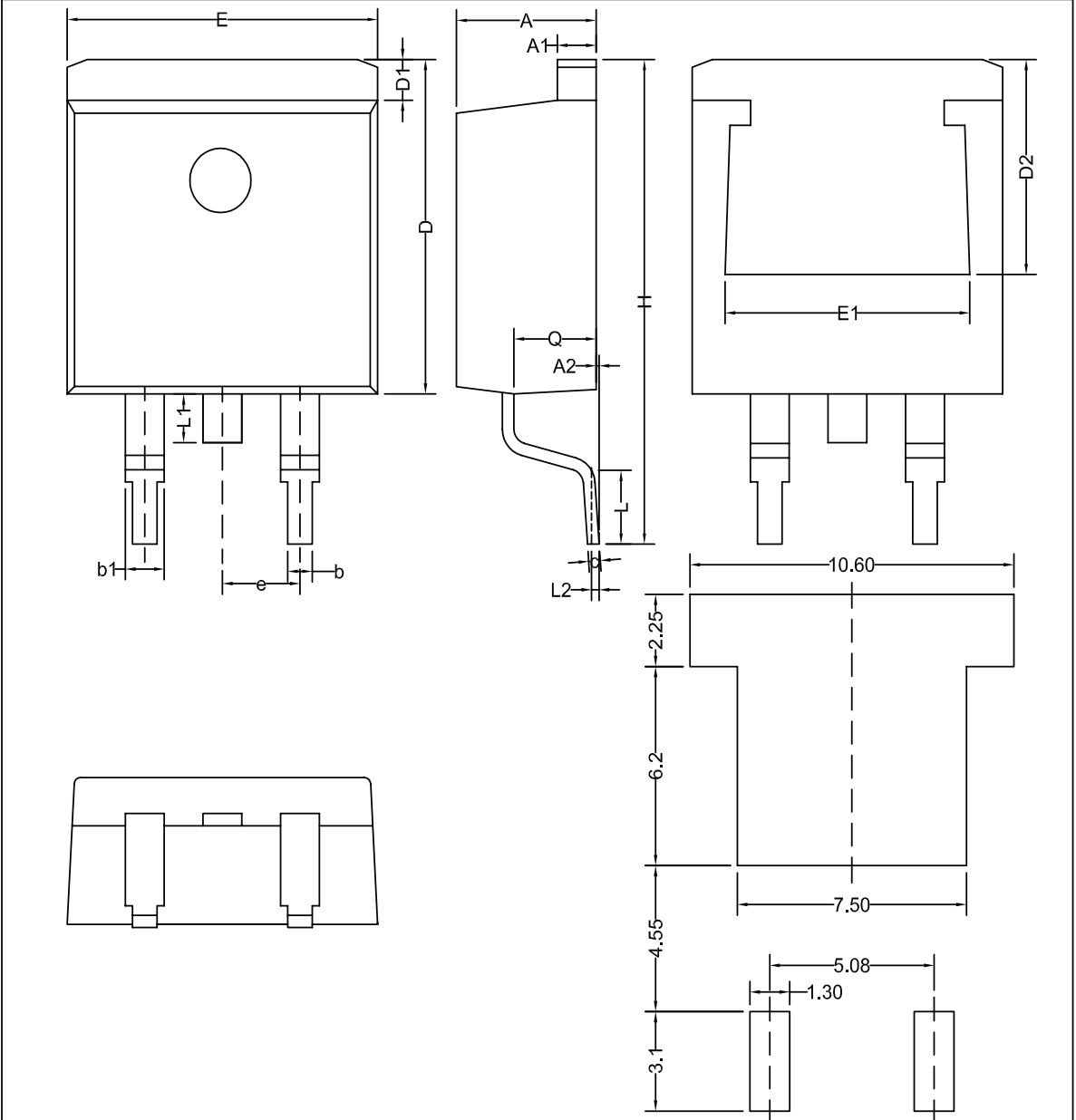


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263



Recommended Footprint

Unit	A	A1	A2	b	b1	c	D	D1	D2	e	E	E1	H	L	L1	L2	Q
min	4.10	1.22	0.00	0.60	1.05	0.34	---	1.20	6.60	2.54 (BSC)	9.70	7.80	14.80	2.10	---	0.25 (BSC)	2.20
max	4.70	1.40	0.25	0.90	1.45	0.64	11.00	1.60	---	---	10.30	---	15.80	2.90	1.75	---	2.79

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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